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Manufacturers of World Class Discrete Semiconductors

2N2646
2N2647

SILICON UNIJUNCTION TRANSISTOR

JEDEC TO-18 CASE*

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N2646, 2N2647 types are silicon PN unijunction transistors designed for general purpose industrial applications.

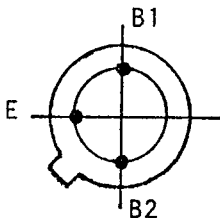
MAXIMUM RATINGS (TA=25°C unless otherwise noted)

	SYMBOL		UNIT
RMS Power Dissipation	P _D (RMS)	300	mW
RMS Emitter Current	I _E (RMS)	50	mA
Peak Pulse Emitter Current	i _E	2.0	A
Interbase Voltage	V _{B2B1}	35	V
Emitter Reverse Voltage	V _{B2E}	30	V
Operating and Storage Junction Temperature	T _J , T _{STG}	-65 TO +150	°C

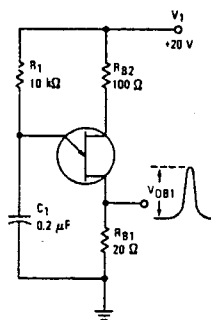
ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N2646		2N2647		UNIT
		MIN	MAX	MIN	MAX	
η	V _{B2B1} =10V [†]	0.56	0.75	0.68	0.82	-
R _{BBO}	V _{B2B1} =3.0V, I _E =0	4.7	9.1	4.7	9.1	kΩ
I _{B2} (MOD)	V _{B2B1} =10V, I _E =50mA	15 TYP		15 TYP		mA
α _{R_{BBO}}	V _{B2B1} =3.0V, T _A =-65°C to +150°C	0.1	0.9	0.1	0.9	%/°C
V _{EB1} (SAT)	V _{B2B1} =10V, I _E =50mA	3.5 TYP		3.5 TYP		V
I _{EO}	V _{B2E} =30V, I _{B1} =0		12		0.2	μA
I _P	V _{B2B1} =25V		5.0		2.0	μA
I _V	V _{B2B1} =20V, R _{B2} =100Ω	4.0	-	8.0	18	mA
V _{OB1}	See test circuit below	3.0		6.0		V

*Conforms to JEDEC TO-18 outline except for lead configuration.



V_{OB1} TEST CIRCUIT



†η TEST CIRCUIT

